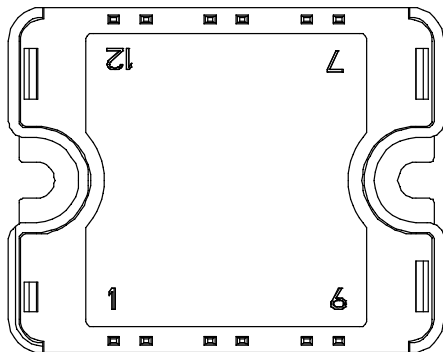
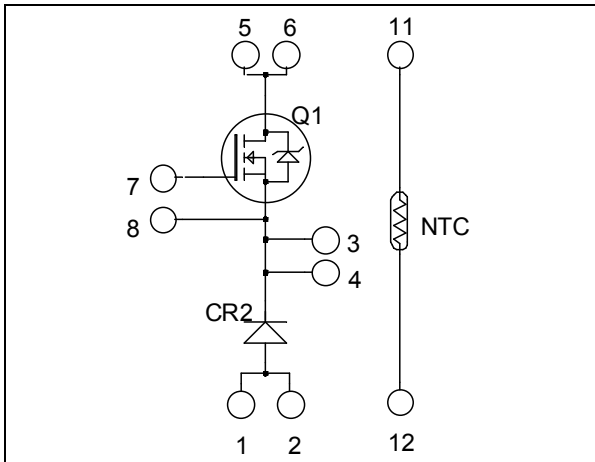


## Buck chopper Super Junction MOSFET Power Module

$V_{DSS} = 600V$   
 $R_{DSon} = 24m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 95A \text{ @ } T_c = 25^\circ C$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features


- **COOLMOS**  
Power Semiconductors
  - Ultra low  $R_{DSon}$
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
  - Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	600	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	95
		$T_c = 80^\circ C$	70
$I_{DM}$	Pulsed Drain current	260	
$V_{GS}$	Gate - Source Voltage	$\pm 20$	V
$R_{DSon}$	Drain - Source ON Resistance	24	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	462
$I_{AR}$	Avalanche current (repetitive and non repetitive)	15	A
$E_{AR}$	Repetitive Avalanche Energy	3	mJ
$E_{AS}$	Single Pulse Avalanche Energy	1900	

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$			350	$\mu\text{A}$
		$T_j = 25^\circ\text{C}$				
		$V_{GS} = 0V, V_{DS} = 600V$			600	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 47.5A$			24	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5\text{mA}$	2.1	3	3.9	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			200	$\text{nA}$

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$C_{iss}$	Input Capacitance	$V_{GS} = 0V ; V_{DS} = 25V$ $f = 1\text{MHz}$		14.4		nF	
$C_{oss}$	Output Capacitance				17		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 300V$ $I_D = 95A$		300		nC	
$Q_{gs}$	Gate – Source Charge				68		
$Q_{gd}$	Gate – Drain Charge				102		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (<math>125^\circ\text{C}</math>)</b> $V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 95A$ $R_G = 2.5\Omega$		21		ns	
$T_r$	Rise Time				30		
$T_{d(off)}$	Turn-off Delay Time				100		
$T_f$	Fall Time				45		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>25^\circ\text{C}</math></b> $V_{GS} = 10V ; V_{Bus} = 400V$ $I_D = 95A ; R_G = 2.5\Omega$		1350		$\mu\text{J}$	
$E_{off}$	Turn-off Switching Energy				1040		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ <math>125^\circ\text{C}</math></b> $V_{GS} = 10V ; V_{Bus} = 400V$ $I_D = 95A ; R_G = 2.5\Omega$		2200		$\mu\text{J}$	
$E_{off}$	Turn-off Switching Energy				1270		

**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ\text{C}$		100	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		500	
$I_F$	DC Forward Current	$T_c = 80^\circ\text{C}$		100		A
$V_F$	Diode Forward Voltage	$I_F = 100A$		1.6	2	V
		$I_F = 200A$		2		
		$I_F = 100A$	$T_j = 125^\circ\text{C}$		1.3	
$t_{rr}$	Reverse Recovery Time	$I_F = 100A$ $V_R = 400V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		160	ns
			$T_j = 125^\circ\text{C}$		220	
$Q_{rr}$	Reverse Recovery Charge	$I_F = 100A$ $V_R = 400V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		290	nC
			$T_j = 125^\circ\text{C}$		1530	

## Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R <sub>thJC</sub>	Junction to Case Thermal Resistance	Transistor		0.27	°C/W	
		Diode		0.55		
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz	2500			V	
T <sub>J</sub>	Operating junction temperature range	-40		150	°C	
T <sub>STG</sub>	Storage Temperature Range	-40		125		
T <sub>C</sub>	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				80	g

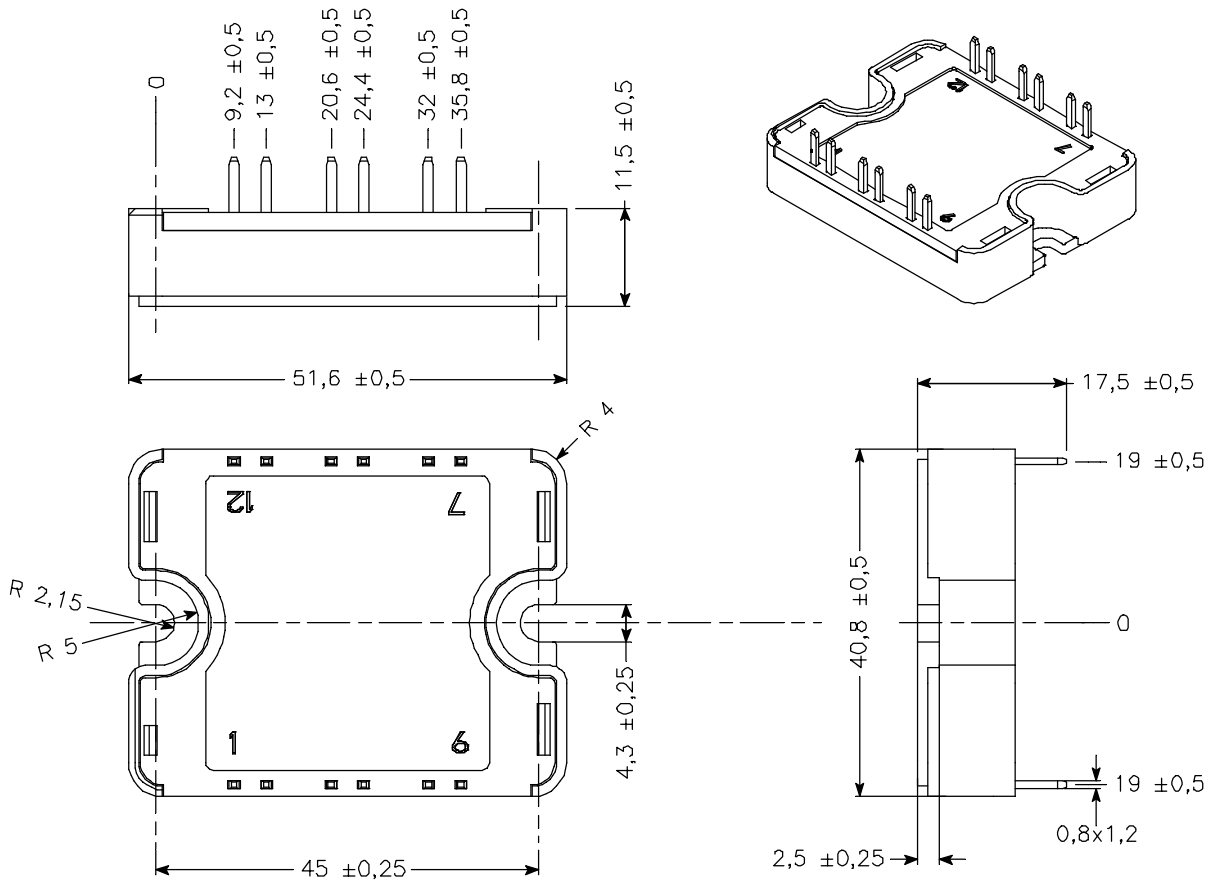
## Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>25</sub>	Resistance @ 25°C		50		kΩ
B <sub>25/85</sub>	T <sub>25</sub> = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right]}$$

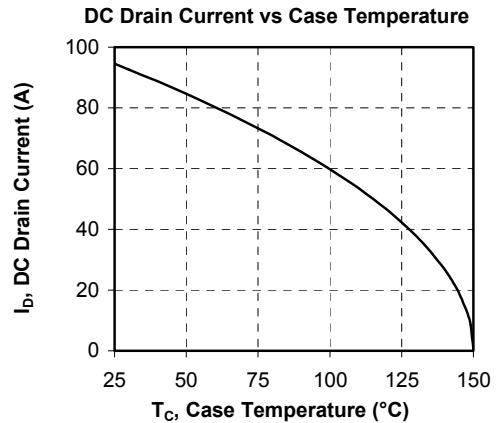
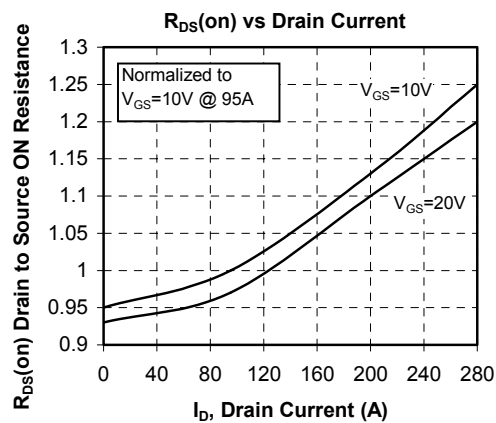
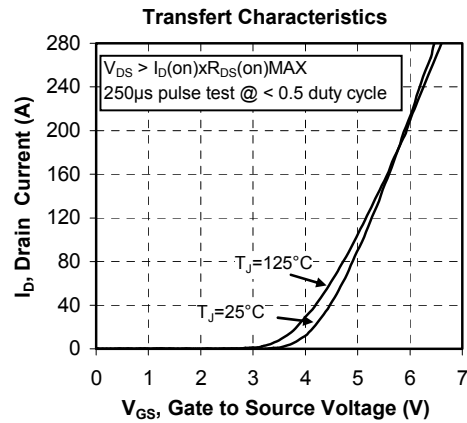
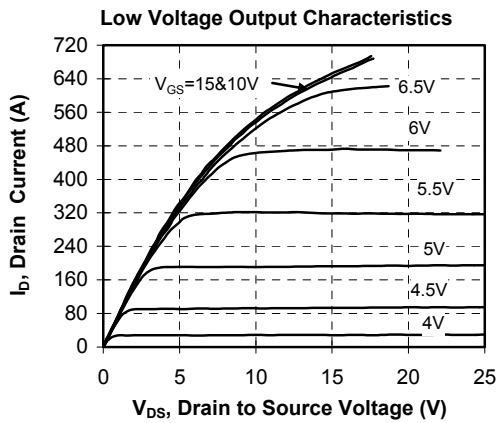
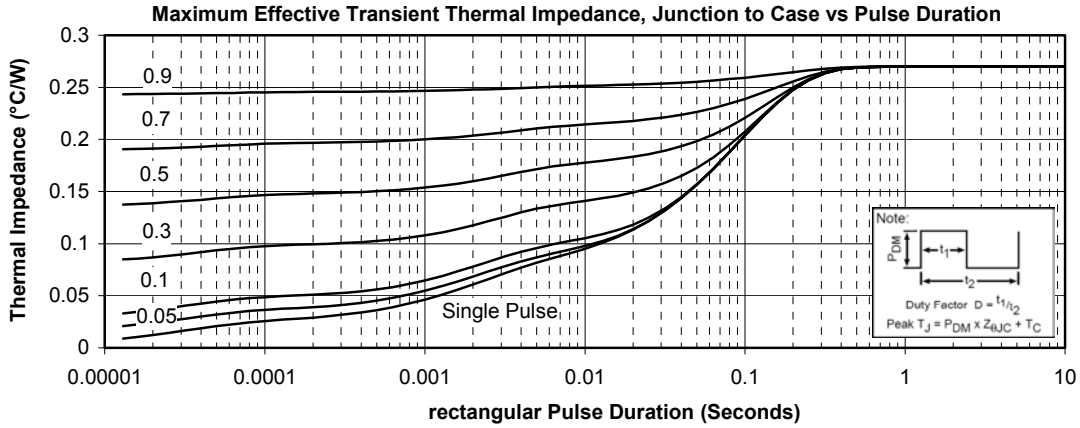
T: Thermistor temperature  
 R<sub>T</sub>: Thermistor value at T

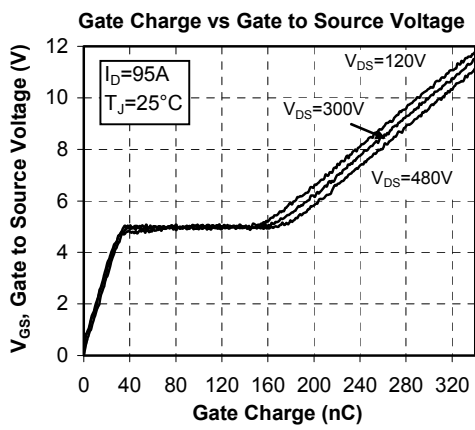
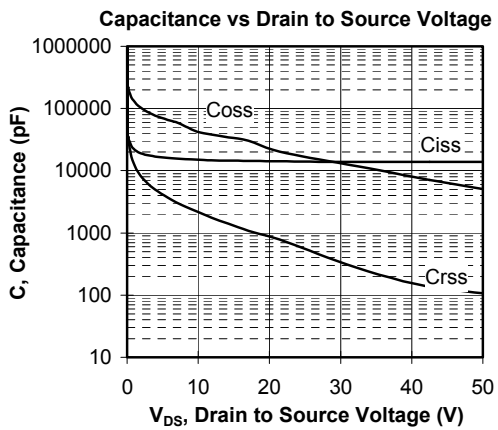
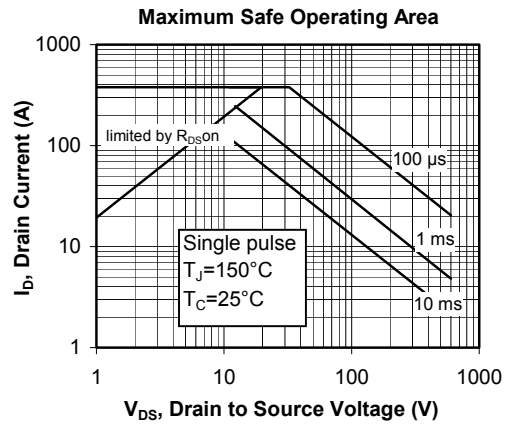
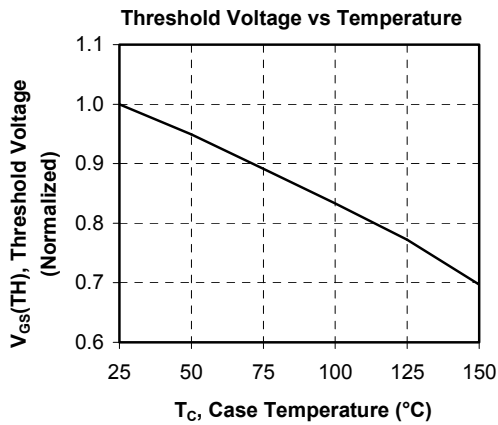
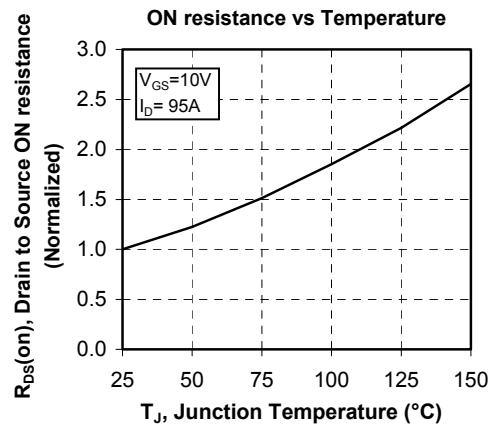
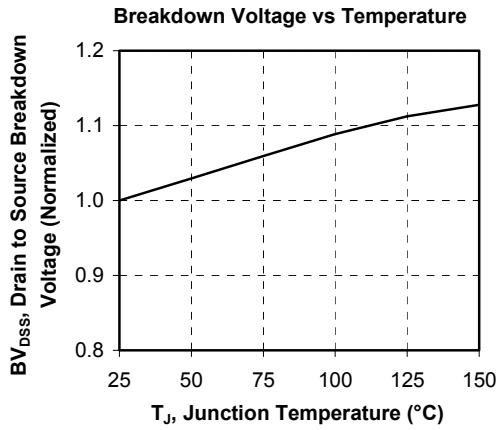
## SP1 Package outline (dimensions in mm)

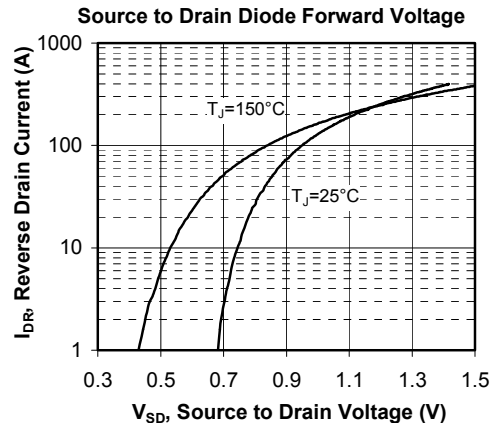
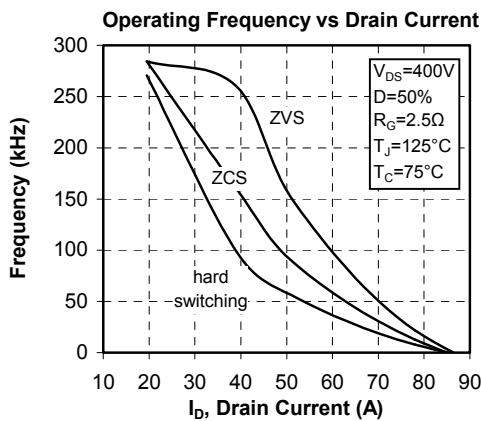
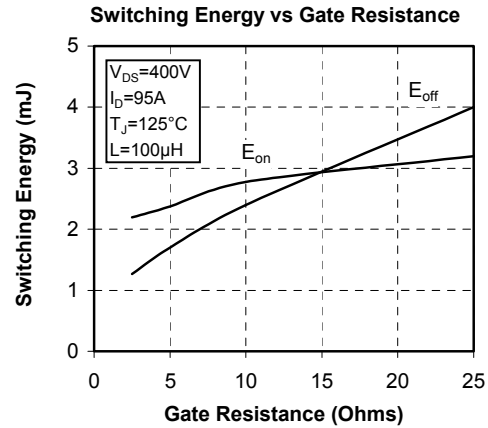
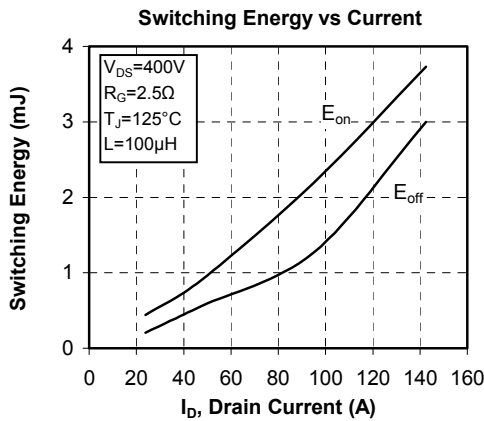
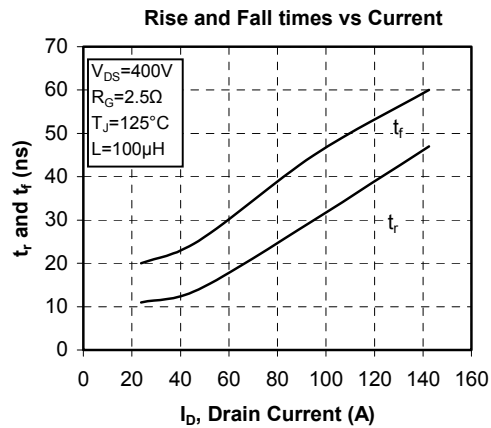
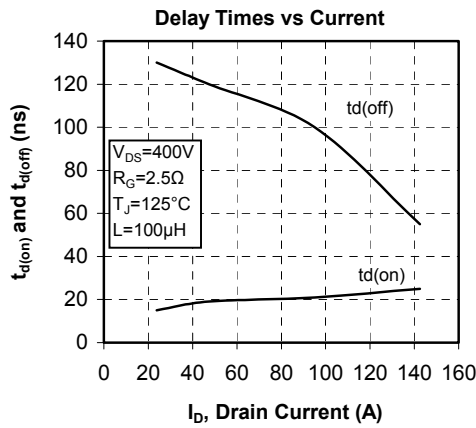


See application note 1904 - Mounting Instructions for SP1 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve







“COOLMOS™” comprise a new family of transistors developed by Infineon Technologies AG. “COOLMOS” is a trademark of Infineon Technologies AG”.

Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.